

# 2SD1318

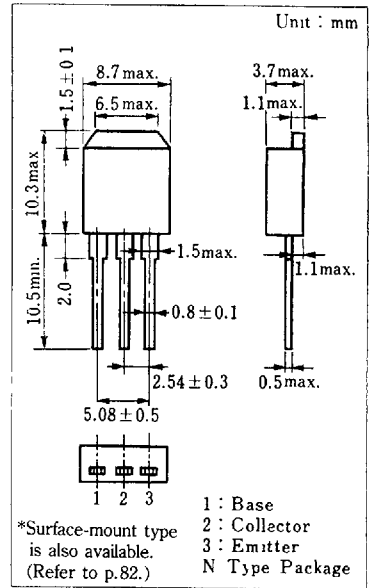
Silicon NPN Triple-Diffused Planar Darlingtone Type

Medium Speed Power Switching

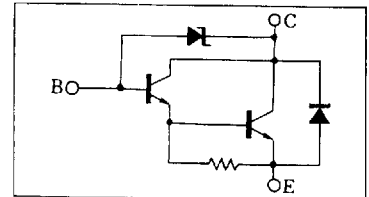
### Features

- 30V Zener diode built-in between C and B
- Very small fluctuation in breakdown voltages
- Large energy handling capability
- High speed switching
- "N Type" package configuration with a cooling fin for direct soldering on PC board of a small-size electronic equipment

### Package Dimensions



### Inner Circuit



### Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Value	Unit	
Collector-base voltage	$V_{CB0}$	$30 \pm 5$	V	
Collector-emitter voltage	$V_{CE0}$	$30 \pm 5$	V	
Emitter-base voltage	$V_{EB0}$	7	V	
Peak collector current	$I_{CP}$	12	A	
Collector current	$I_C$	8	A	
Collector power dissipation	$P_C$	$T_C = 25^\circ C$	45	W
		$T_a = 25^\circ C$	13	
Junction temperature	$T_J$	150	°C	
Storage temperature	$T_{str}$	-55 ~ +150	°C	

### Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	$I_{CB0}$	$V_{CB} = 25 V, I_C = 0$			100	$\mu A$
Emitter cutoff current	$I_{EB0}$	$V_{EB} = 25 V, I_F = 0$			2	mA
Collector-emitter voltage	$V_{CE0}$	$I_C = 5 mA, I_B = 0$	25		35	V
DC current gain	$h_{FE1}^{*1}$	$V_{CE} = 3 V, I_C = 4 A$	1000		10000	
		$V_{CE} = 3 V, I_C = 8 A$	500			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 4 A, I_B = 8 mA$			1.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 4 A, I_B = 8 mA$			2	V
Transition frequency	$f_T$	$V_{CE} = 10 V, I_C = 0.5 A, f = 1 MHz$		20		MHz
Turn-on time	$t_{on}$	$I_C = 4 A, I_{B1} = 8 mA, I_{B2} = -8 mA, V_{CC} = 20 V$		0.5		$\mu s$
Storage time	$t_{stg}$		4		$\mu s$	
Fall time	$t_f$		1		$\mu s$	
Energy handling capability	$E_{s/b}^{*2}$	$I_C = 2 A, L = 100 mH, R_{BF} = 100 \Omega$	200			mJ

### \*1 $h_{FE1}$ Classifications

Class	R	Q	P
$h_{FE1}$	1000 ~ 2500	2000 ~ 5000	4000 ~ 10000

### \*2 E, b Test method

